

IN THE CLAIMS:

Please amend the claims as indicated below (Note: a marked up version of the amended claims indicated changes made thereof appears at the end of this document). Claims 1-12 have been amended as indicated below, including the introduction of newly submitted claims 13-16:

1. (Amended) A method for forming a wiring bond pad utilized in wire bonding operations on an integrated circuit device, said method comprising the steps of:

configuring a wiring bond pad to comprise a single metal layer, wherein said single metal layer does not share said single metal layer with any other material; and

positioning at least one integrated circuit device below said wiring bond pad to thereby conserve integrated circuit space and improve wiring bond pad efficiency as a result of configuring said wiring bond pad to comprise a single metal layer.

2. (Amended) The method of claim 1 wherein the step of configuring a wiring bond pad to comprise a single metal layer, further comprises the step of:

locating a buffer and bonding layer immediately above said single metal layer.

3. (Amended) The method of claim 1 further comprising the step of:

locating said single metal layer above a plurality of intermetal dielectric layers.

4. (Unamended) The method of claim 3 further comprising the step of:
locating said at least one integrated circuit device below said plurality of intermetal dielectric layers.
5. (Unamended) The method of claim 4 wherein said single metal layer comprises a metal-8 layer.
6. (Amended) The method of claim 4 wherein said plurality of intermetal dielectric layers comprises at least IMD-1 to IMD-7 layers.
7. (Amended) The method of claim 5 6 wherein said metal-8 layer comprises a copper layer.
8. (Unamended) The method of claim 1 wherein said single metal layer comprises a copper layer.
9. (Unamended) The method of claim 8 further comprising the step of:
forming a layer of aluminum film above said single metal layer.
10. (Unamended) The method of claim 9 wherein said layer of aluminum film formed above said single metal layer comprises a layer having a thickness in a range of and including 10KÅ to 20KÅ.
11. (Unamended) The method of claim 9 wherein said single metal layer comprises a copper layer having a thickness of approximately 10KÅ.
12. (Unamended) The method of claim 11 wherein said layer of aluminum film above said single metal layer comprises a buffer and bonding layer.

25.
~~13.~~ (Newly Submitted) A method for forming a wiring bond pad utilized in wire bonding operations on an integrated circuit device, said method comprising the steps of:

configuring a wiring bond pad to comprise a single metal layer, wherein said single metal layer comprises a copper layer;

positioning at least one integrated circuit device below said wiring bond pad to thereby conserve integrated circuit space and improve wiring bond pad efficiency as a result of configuring said wiring bond pad as a single metal layer;

locating said wiring bond pad above a plurality of intermetal dielectric layers, wherein said plurality of intermetal dielectric layers comprises IMD-1 to IMD-7 layers; and

forming a layer of aluminum film above said wiring bond pad, wherein said layer of aluminum film comprises a thickness in a range of and including 10KÅ to 20KÅ.

26.
~~14.~~ (Newly Submitted) The method of claim 13 wherein said single metal layer of said wiring bond pad comprises a copper layer having a thickness of approximately 10KÅ.

27.
~~15.~~ (Newly Submitted) The method of claim 13 wherein said layer of aluminum film above said wiring bond pad comprises a buffer and bonding layer.

28.
~~16.~~ (Newly Submitted) The method of claim 13 wherein said layer of aluminum film above said wiring bond pad comprises a bonding layer.

REMARKS

In further support of the claims presented and amendments thereof, Applicants submit the following remarks.